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April 1st, 2010 Renesas Electronics Corporation

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MOS FIELD EFFECT TRANSISTOR

2SK3434

SWITCHING

N-CHANNEL POWER MOS FET

DESCRIPTION

The 2SK3434 is N-channel MOS Field Effect Transistor designed for high current switching applications.

FEATURES

- Super low on-state resistance
- $R_{DS(on)1} = 20 \text{ m}\Omega \text{ MAX.} (V_{GS} = 10 \text{ V}, \text{ ID} = 24 \text{ A})$
- $R_{\text{DS(on)2}}=31\ m\Omega$ MAX. (VGs = 4.0 V, ID = 24 A)
- Low C_{iss} : $C_{iss} = 2100 \, pF \, TYP$.
- Built-in gate protection diode

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (VGs = 0 V)	VDSS	60	V
Gate to Source Voltage ($V_{DS} = 0 V$)	Vgss	±20	V
Drain Current (DC) (Tc = 25°C)	ID(DC)	±48	Α
Drain Current (pulse) Note1	D(pulse)	±120	Α
Total Power Dissipation (Tc = 25°C)	Рт	56	W
Total Power Dissipation ($T_A = 25^{\circ}C$)	Рт	1.5	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	–55 to +150	°C
Single Avalanche Current Note2	las	28	А
Single Avalanche Energy Note2	Eas	78	mJ

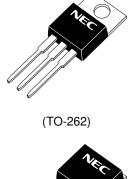
Notes 1. PW \leq 10 μ s, Duty cycle \leq 1%

2. Starting T_{ch} = 25°C, V_{DD} = 30 V, R_G = 25 Ω , V_{GS} = 20 \rightarrow 0 V

ORDERING INFORMATION

PART NUMBER	PACKAGE	
2SK3434	TO-220AB	
2SK3434-S	TO-262	
2SK3434-ZJ	TO-263	
2SK3434-Z	TO-220SMD ^{Note}	

Note TO-220SMD package is produced only in Japan.



(TO-220AB)



(TO-263, TO-220SMD)



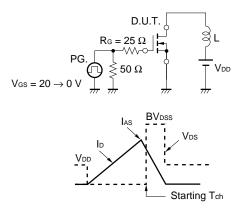
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ELECTRICAL CHARACTERISTICS (TA = 25°C)

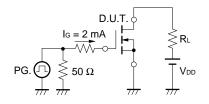
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Drain Current	IDSS	$V_{DS} = 60 V, V_{GS} = 0 V$			10	μA
Gate Cut-off Voltage	V _{GS(off)}	$V_{DS} = 10 V, I_{D} = 1 mA$	1.5	2.0	2.5	V
Forward Transfer Admittance	y fs	Vds = 10 V, Id = 24 A	13	27		S
Drain to Source On-state Resistance	RDS(on)1	Vgs = 10 V, Id = 24 A		16	20	mΩ
	RDS(on)2	Vgs = 4.0 V, Id = 24 A		22	31	mΩ
Input Capacitance	Ciss	V _{DS} = 10 V		2100		pF
Output Capacitance	Coss	Vgs = 0 V		340		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		170		pF
Turn-on Delay Time	td(on)	$V_{DD} = 30 V, I_D = 24 A$		40		ns
Rise Time	tr	Vgs = 10 V		400		ns
Turn-off Delay Time	td(off)	Rg = 10 Ω		120		ns
Fall Time	tr			160		ns
Total Gate Charge	QG	Vdd = 48 V		40		nC
Gate to Source Charge	Qgs	Vgs = 10 V		7		nC
Gate to Drain Charge	Qgd	ID = 48 A		11		nC
Body Diode Forward Voltage	VF(S-D)	IF = 48 A, VGS = 0 V		1.0		V
Reverse Recovery Time	trr	IF = 48 A, VGS = 0 V		43		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/µs		61		nC

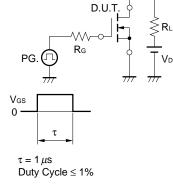
TEST CIRCUIT 1 AVALANCHE CAPABILITY

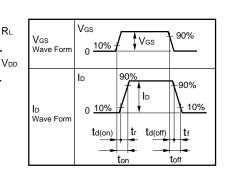
TEST CIRCUIT 2 SWITCHING TIME



TEST CIRCUIT 3 GATE CHARGE







TOTAL POWER DISSIPATION vs.

80 100

Tc - Case Temperature - °C

140

160

120

CASE TEMPERATURE

70

60

50

40

30

20

10

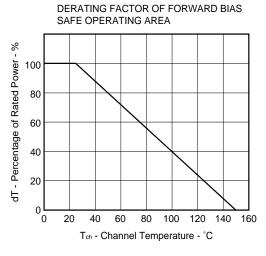
0

0

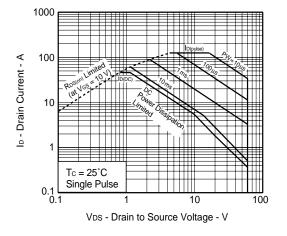
20 40 60

PT - Total Power Dissipation - W

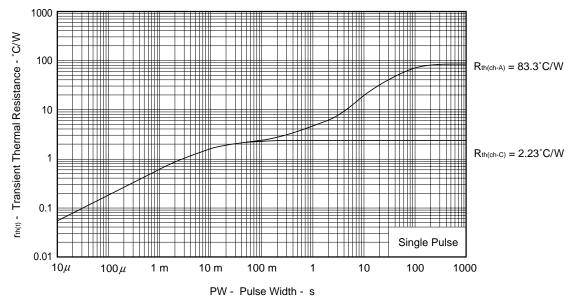
TYPICAL CHARACTERISTICS ($T_A = 25^{\circ}C$)







TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



Data Sheet D14603EJ3V0DS

FORWARD TRANSFER CHARACTERISTICS

0.8

20

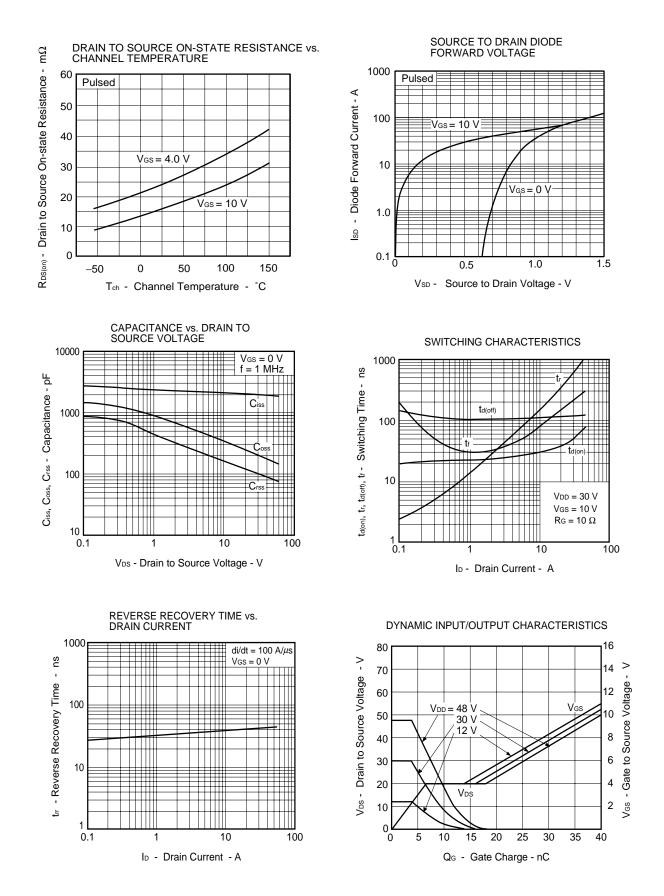
150

Tch - Channel Temperature - °C

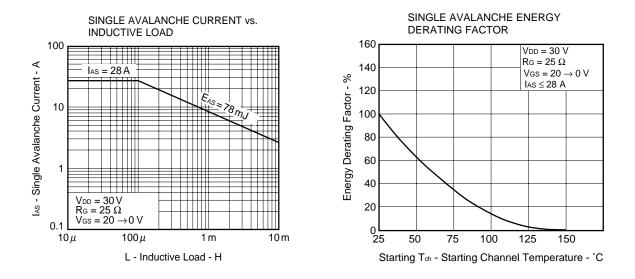
DRAIN CURRENT vs.

DRAIN TO SOURCE VOLTAGE 1000 Pulsed 50 ∢ 100 ∢ 40 Drain Current -Drain Current T_A = −40°C 30 10 = 40 0 ≣ 25°C ≦ 75°C Vgs=10 V -150°C 20 --1 Vgs = 4.0 V 10 Pulsed 0.1 **–** 1.0 $V_{DS} = 10 V$ 0 0 0.2 0.4 0.6 4.0 5.0 6.0 2.0 3.0 VDS - Drain to Source Voltage - V VGS - Gate to Source Voltage - V DRAIN TO SOURCE ON-STATE RESISTANCE vs. FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT - mΩ GATE TO SOURCE VOLTAGE RDS(on) - Drain to Source On-state Resistance ŝ 100 50 $V_{DS} = 10 V$ Pulsed | yfs | - Forward Transfer Admittance Pulsed 40 10 30 TA = -40°C 1 25°C 75°C 20 $I_{D} = 24 A$ 150°C 0.1 10 0.01 0 5 10 15 0.01 0.1 1 10 100 0 Vgs - Gate to Source Voltage - V ID - Drain Current - A DRAIN TO SOURCE ON-STATE $R_{DS(on)}$ - Drain to Source On-state Resistance - m Ω **RESISTANCE vs. DRAIN CURRENT** GATE TO SOURCE THRESHOLD VOLTAGE vs. CHANNEL TEMPERATURE > 40 Pulsed Gate to Source Threshold Voltage -3.0 $V_{DS} = 10 V$ Ip = 1 mA 2.5 30 2.0 $V_{GS} = 4.0 V$ 11111 20 1.5 1.0 Vgs = 10 V 10 0.5 ÷ V_{GS(off)} 0 0 -50 0 50 100 10 100 1000

ID - Drain Current - A

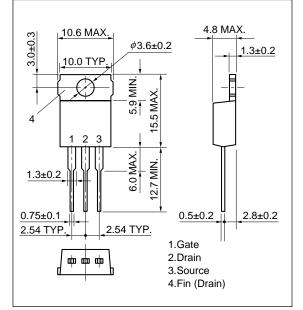


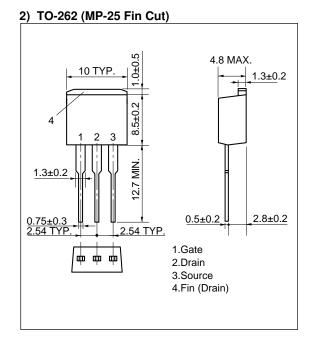
Data Sheet D14603EJ3V0DS



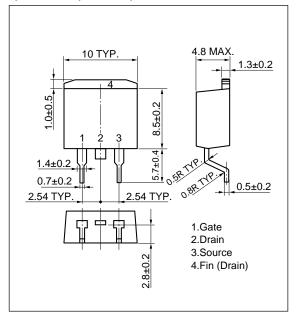
* PACKAGE DRAWINGS (Unit: mm)

1) TO-220AB (MP-25)

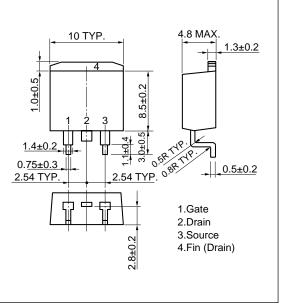




3) TO-263 (MP-25ZJ)

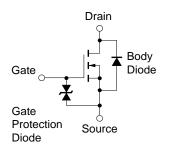


4) TO-220SMD (MP-25Z)^{Note}



Note This package is produced only in Japan.

EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

Data Sheet D14603EJ3V0DS

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